

Amendment under 37 CFR § 1.111
Serial No. 10/807,327
Attorney Docket No. 042271

AMENDMENTS TO THE SPECIFICATION

Please amend the specification as follows:

Title of The Invention

Please amend the title as follows:

SEMICONDUCTOR DEVICE WITH A FERROELECTRIC CAPACITOR AND
~~MANUFACTURING METHOD THEREOF~~

Specification

Please amend the paragraph from page 8, line 2 to page 9, line 12 as follows:

Hereinbelow, a first embodiment of the present invention will be described. Fig. 2 is a layout illustrating a configuration of a semiconductor device (ferroelectric memory) according to the first embodiment of the present invention, in which a straight line connecting the source and the drain of the transistor extends in a direction substantially inclined at an angle of 45 degrees to the longitudinal and lateral directions of the array constituted by the plurality of ferroelectric capacitors, also in which the line connecting the source and the drain of one of the two transistors substantially coincides with the line connecting the source and the drain of the other one of the two transistors. Fig. 3 is a sectional view taken along the I-I line in Fig. 2. Fig. 4A is a sectional

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view taken along the II-II line in Fig. 2. Fig. 4B is a sectional view taken along the III-III line in Fig. 2. Fig. 5 is a sectional view taken along the IV-IV line in Fig. 2.

Please amend the paragraph from page 15, line 17-22 as follows:

Subsequently, a second embodiment of the present invention will be described. Fig. 6 is a layout illustrating a configuration of a semiconductor device (ferroelectric memory) according to the second embodiment of the present invention, in which the line connecting the source and the drain of one of the two transistors is substantially orthogonal to the line connecting the source and the drain of the other one of the two transistors. Fig. 7 is a sectional view taken along the I-I line in Fig. 6.